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MITSUBISHI SEMICONDUCTOR <GaAs FET>

MGF1953A

Microwave Power MES FET (Leadless Ceramic Package)

## **DESCRIPTION**

The MGF1953A is designed for use in S to Ku band power amplifiers.

The lead-less ceramic package assures minimum parasitic losses.

### **FEATURES**

High gain and High P1dB

Glp=6.0dB, P1dB=20dBm (Typ.) @ f=12GHz

## **APPLICATION**

S to Ku band power Amplifiers

## QUALITY GRADE

GG

## RECOMMENDED BIAS CONDITION

 $V_{DS}=6V$ ,  $I_{D}=100mA$ 

## ORDERING INFORMATION

Tape & reel 3000pcs./reel

## **Outline Drawing**

Fig.1

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
V <sub>GDO</sub>	Gate to drain voltage	-10	V
V <sub>GSO</sub>	Gate to source voltage	-10	V
I <sub>D</sub>	Drain current	400	mA
PT	Total power dissipation	1	W
T <sub>ch</sub>	Channel temperature	125	°C
T <sub>stg</sub>	Storage temperature	-65 to +125	°C

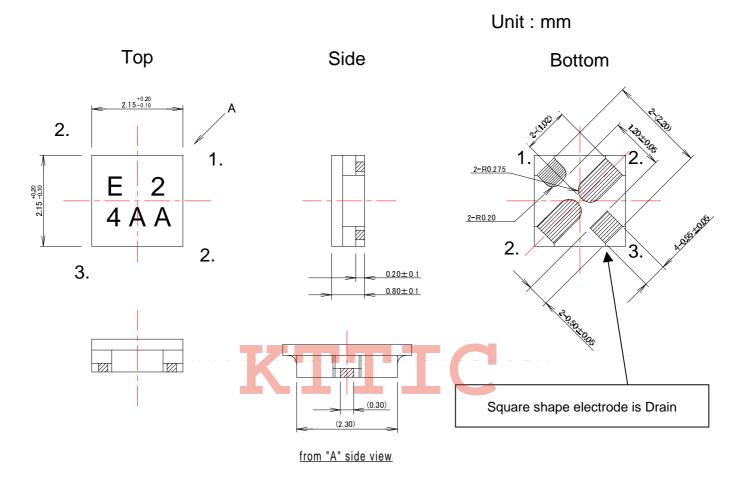
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## ELECTRICAL CHARACTERISTICS (Ta=25°C)

Synbol	Parameter	Test conditions	Limits		Unit	
			MIN.	TYP.	MAX	
V(BR)GDO	Gate to drain breakdown voltage	lg=-100μA	-10	-15		V
I <sub>DSS</sub>	Saturated drain current	V <sub>GS</sub> =0V,V <sub>DS</sub> =3V	105	200	400	mA
V <sub>GS(off)</sub>	Gate to source cut-off voltage	V <sub>DS</sub> =3V,I <sub>D</sub> =1mA	-0.3	-1.4	-3.5	V
P1dB	Output Power at 1dB gain	V <sub>DS</sub> =4V,ID=100mA	18	20		dBm
	Compression	f=12GHz				
Glp	Linear Power Gain	V <sub>DS</sub> =4V,ID=100mA	4	6		dB
		f=12GHz,Pin=5dBm				

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Fig.1

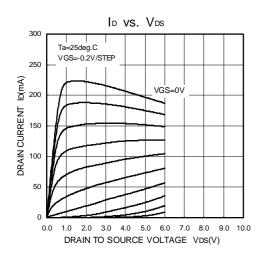


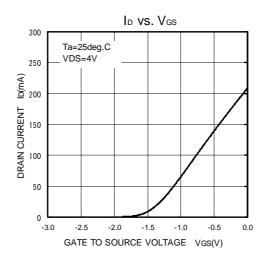
- 1. Gate
- 2. Source
- 3. Drain

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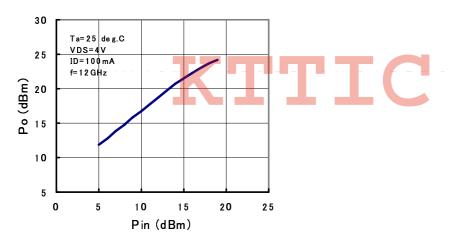
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## TYPICAL CHARACTERISTICS (Ta=25°C)





Po vs. Pin



(3/5)

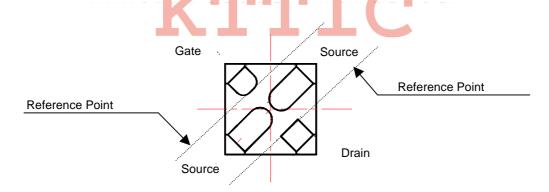
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## **S PARAMETERS**

(Conditions: VDS=4V,ID=100mA,Ta=25deg.C)

f	S	11	S	21	S	12	S	22	K	MAG/MSG
(GHz)	Mag.	Angle	Mag.	Angle	Mag.	Angle	Mag.	Angle		(dB)
1	0.907	-51.1	8.288	143.0	0.026	63.3	0.148	-62.0	0.40	25.0
2	0.775	-95.1	6.461	112.7	0.041	42.5	0.161	-105.9	0.73	21.9
3	0.702	-121.5	5.090	95.3	0.049	34.4	0.173	-123.3	0.99	20.1
4	0.674	-144.5	4.128	79.9	0.055	28.9	0.187	-138.9	1.16	16.3
5	0.661	-161.3	3.521	66.9	0.060	23.7	0.190	-145.1	1.29	14.5
6	0.653	-175.4	3.105	54.6	0.065	20.8	0.185	-146.9	1.38	13.1
7	0.650	170.8	2.810	41.7	0.071	17.5	0.175	-147.3	1.41	12.2
8	0.650	157.4	2.609	28.9	0.078	12.7	0.164	-149.1	1.40	11.5
9	0.642	143.3	2.440	16.2	0.086	6.9	0.142	-154.0	1.40	10.8
10	0.640	127.4	2.270	2.4	0.096	-0.1	0.114	-165.1	1.39	10.0
11	0.623	109.0	2.091	-12.5	0.103	-10.3	0.083	166.0	1.50	8.9
12	0.619	90.0	1.908	-27.6	0.106	-20.4	0.085	113.6	1.63	7.9
13	0.634	71.7	1.710	-42.4	0.108	-29.8	0.140	75.8	1.75	7.0
14	0.666	54.3	1.507	-57.2	0.107	-41.2	0.217	54.5	1.86	6.2
15	0.713	39.4	1.314	-70.2	0.105	-50.7	0.300	41.8	1.89	5.5
16	0.769	27.0	1.139	-82.8	0.101	-59.9	0.378	32.0	1.84	5.2
17	0.822	15.6	0.976	-95.2	0.097	-68.4	0.455	23.4	1.76	5.0
18	0.865	5.9	0.821	-107.2	0.091	-77.2	0.513	15.3	1.67	4.7





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